
INFORMATION DISCLOSURE				ATTY, DOCKET NO.	1	SERIAL NO				
					67161-039	.	10/615,7			
CITATION IN AN				07 10 1-033		10/0 10,1				
/\PA	OIPE APPLICATION									
10		PPL	JCATION							
1/	5.1				APPLICANT					
FEB 2 8 201	[8 a				Hideto HIDAKA					
TEO .	떪									
\ E	E/	'nт	O 1440)		FILING DATE GRO		GROUP	OUP		
(PTO-1449)					July 10, 2003 28:		2824	24		
TRADEN			¥1	(C. 10 A (C)C)N/O						
			U	.S. PAIENI	DOCUMENTS					
EXAMINER'S	CITE			Publication Date	Name of Patentee or Applicant of Cited			Pages, Columns, Lines, Whe		
INITIALS NO.		Number-Kind Codes (# known)		MM-DD-YYYY	Document		Rejev	Relevant Passages or Relevant Figures Appear		
	Ì							1 1901 00 1 4	ppeu.	
	 	υs	6,577,527 B2	6/10/2003	Freitag et al.					
- Com	 	US								
	 	US	\							
	 	US								
		US			···					
US					 		- 			
	 	US								
		US			 					
	 	US								
	 	US			-					
<u> </u>	 	US			 					
ļ		US								
	 	US						······		
		US					_			
	ــــــــــــــــــــــــــــــــــــــ	100	······	FOREIGN PAT	ENT DOCUMENTS	*-	<u> </u>			
EXAMINER'S		E E	reign Patent Document	Publication Date	Name of Patentee or	Page C	clumns, Lines	Tra	anslation	
INITIALS	CITE Country Codes-Number 4-4			MM-DD-YYYY	Applicant of Cited Document					
	NO.		Codes (if known)			Figures Appear		Yes No		
	 	†			,					
		 								
	1	1		 		1				
	1	T		<u> </u>						
		t				1				
	1	•	OTHER A	RT (Including Autho	r, Title, Date, Pertinent Pages, E	tc.)				
EXAMINER'S	1	Inclu	de name of the author (in	CAPITAL LETTERS), title of the article (when appro-	oriate), title	of the item (bo	ok, magazint	3.	
INITIALS	CITE	journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where								
	NO.	publ	ished.							
	-	1								
		┼								
								- 		
										
EXAMINER DATE CONSIDERED										
	inh		+ hunos		6/2	W/0	ර			
*EYAMINED: Initial			1	1	a with MDED 609. Draw line thro	uab citatia	n if not in earfar	mana and	hat considered	

*EXAMINER: Initial if reference considered, whether or roycitation is in conformance with MFET 605. Draw the direction in Include copy of this form with next communication to applicant.

1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.

R	SIP	E 40	
BETT	M 5	o and	SEELCE

								SHEET	L OF L	
THE PROPERTY OF THE PROPERTY O				ATTY. DOCKET NO. 67161-039	SERIAL NO. 10/615,777					
			ON IN AN ICATION							
	AP	PL	CATION		APPLICANT Hideto HIDAKA					
(PTO-1449)					FILING DATE July 10, 2003	GR	OUP 11			
				U.S. PATENT	DOCUMENTS					
XAMINER'S INITIALS	CITE	Numb	Documt Number ter-Kind Codts: p second	Publication Date NBM-DD-YYYY	Name of Patentee or Applica Document	nt of Cited	Pages, Releva	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear		
	NO.	US 2002/0172073		11/21/2002	HIDAKA					
$\Omega \Omega$	A1	33	10/327,888	12/26/2002	HIDAKA			Not co	nsidered	
		us us	10.321,000				a	P 11/26	12004	
	 	us					 '			
		us								
	 -	us					+			
		us			 					
		US			 		+			
		US		 	 					
		us			 					
	ļ	US				7				
	├	us				\overline{Z}				
	 	us					`			
			<u></u>		TENT DOCUMENTS	Dance Col	umne Lines	To	anslation	
EXAMINER'S	Т	Foreign Patent Document		Publication Date MYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Figures Appear				
INITIALS	NO.	Country Codes - Number + - Kind Codes (if known)						L	No.	
•								Yes	No	
-00		+-	JP 2002-170375	06/14/2002	HIRAL			abstract		
ap		+						-	 	
	- 	+-		77 .		<u> </u>		 		
	1	1						-		
	1			J	nor, Title, Date, Pertinent Pages, F	(tr.)				
							of the item (bo	ook, magazir	18,	
EXAMINER'S INITIALS	CITE NO.	iou	rnal, serial, symposium, c blished.	Stated territ name to	agolog, version care and a company					
GD.	1	\top	SCHEUERLEIN, et al. "A 10ns Read and Write Non-Volatile Memory Array Using a Magnetic Tunnel Junction and FET Switch in Each Cell' IEEE International Solid-State Circuits Conference (2000) TA 7.2 DURLAM, et al. "Nonvotatile RAM Based on Magnetic Tunnel Junction Elements" IEEE International Solid-State Circuits Conference (2000) TA 7.3							
-	+-	+	DURLAM, et al. "Nonvota	tite RAM Based on t	Magnetic Tunnel Junction Element	P. IFFF tute	madonai Sub	USBE CITE		
	-	+	NAJI, et al. "A 256Nb 3.0V	1T1MJT Nonvolatile	Magnetoresistive RAM* IEEE Int (2001) TA 7.8	ternational S	did-State Cin	cuits Confere	emze	
up										
		<u></u> -	- Lung		11/26/20	DATE COS	nsidered	5/10/0	54	
	Cen	h	+ hung		1) 26 / 20	much citation	if not in con			

*EXAMPNER: britial if reference considered, whether or dot citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not consultation to applicant.

1 Applicant's unique citation designation number (obstand). 2 Applicant is to place a check mark here if English language Translation is attached.